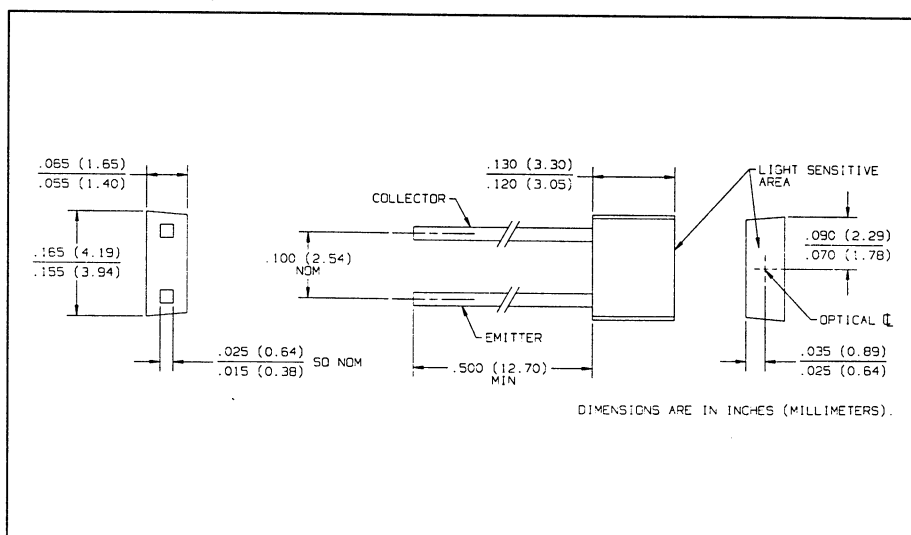
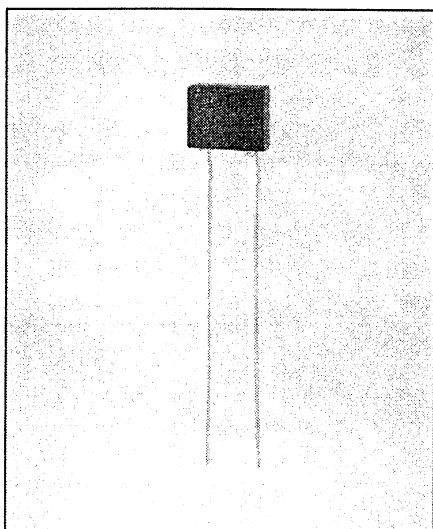


NPN Silicon Photodarlington Types OP538FA, OP538FB, OP538FC



Features

- Flat lensed for wide acceptance angle
- Easily stackable on 0.100 inch (2.54 mm) hole centers
- Low cost plastic package
- Mechanically and spectrally matched to the OP168F and OP268F series of infrared emitting diodes

Description

The OP538F series consists of NPN silicon photodarlington mounted in flat lensed, black plastic, "end looking" packages. The flat sensing surface allows an acceptance half angle of 65° measured from the optical axis to the half power point. The black plastic package significantly reduces ambient light noise. These devices can be mounted on 0.100" (2.54 mm) hole centers making them an ideal low cost alternative to hermetic OP600 sensors.

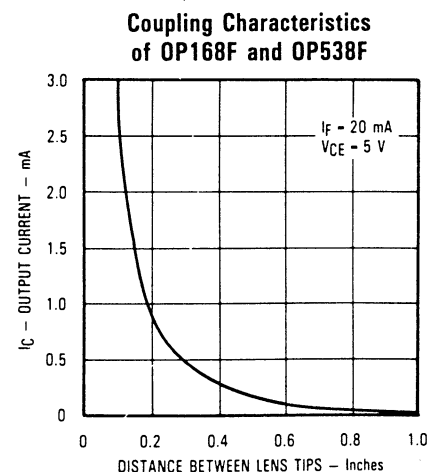
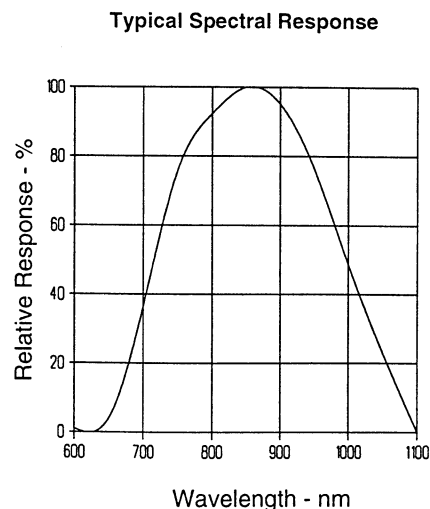
Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5.0 V
Storage and Operating Temperature Range	-40° C to +100° C
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron]	260° C ⁽¹⁾
Power Dissipation	100 mW ⁽²⁾

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds max. when flow soldering. Maximum 20 grams force may be applied to the leads when soldering.
- (2) Derate linearly 1.33 mW/° C above 25° C.
- (3) Light source is an unfiltered GaAs LED with a peak emission wavelength of 935 nm and a radiometric intensity level which varies less than 10% over the entire lens surface of the phototransistor being tested.
- (4) Due to high gain of photodarlington, a load resistor should be used to avoid thermal runaways.

Typical Performance Curves

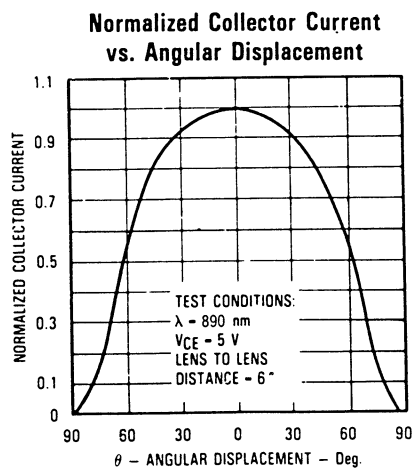
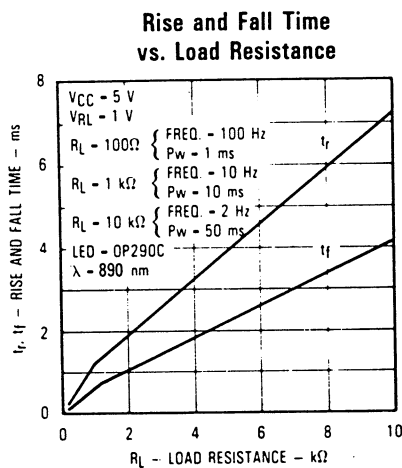
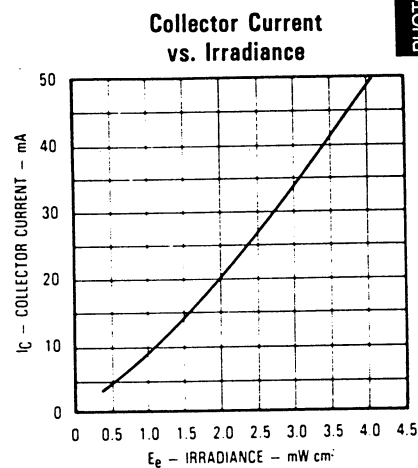
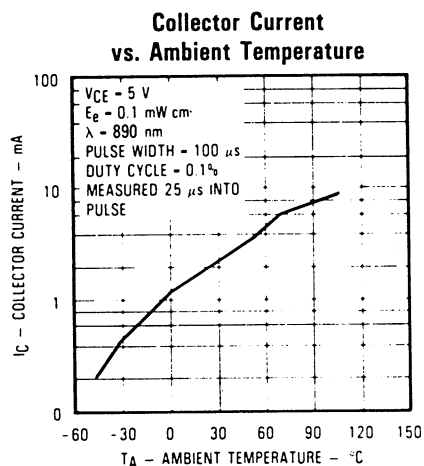
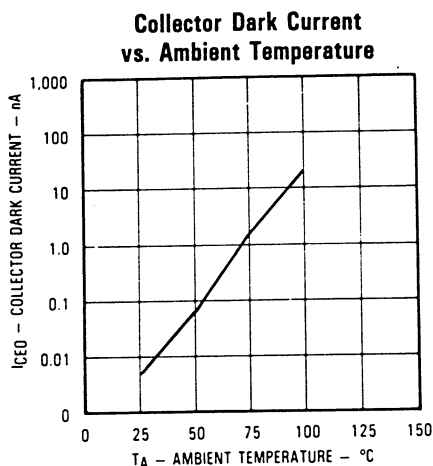


Types OP538FA, OP538FB, OP538FC

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
$I_{C(ON)}^{(4)}$	On-State Collector Current	OP538FC 1.1 OP538FB 2.3 OP538FA 6.8		20.5	mA	$V_{CE} = 5.0\text{ V}$, $E_e = 0.5\text{ mW/cm}^{2(3)}$ $V_{CE} = 5.0\text{ V}$, $E_e = 0.5\text{ mW/cm}^{2(3)}$ $V_{CE} = 5.0\text{ V}$, $E_e = 0.5\text{ mW/cm}^{2(3)}$
I_{CEO}	Collector-Dark Current			225	nA	$V_{CE} = 10.0\text{ V}$, $E_e = 0$
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	15.0			V	$I_C = 1.00\text{ mA}$, $E_e = 0$
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5.0			V	$I_E = 100\text{ }\mu\text{A}$, $E_e = 0$
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage			1.00	V	$I_C = 0.5\text{ mA}$, $E_e = 0.5\text{ mW/cm}^{2(3)}$

Typical Performance Curves



Switching Time Test Circuit

